

Fig.1

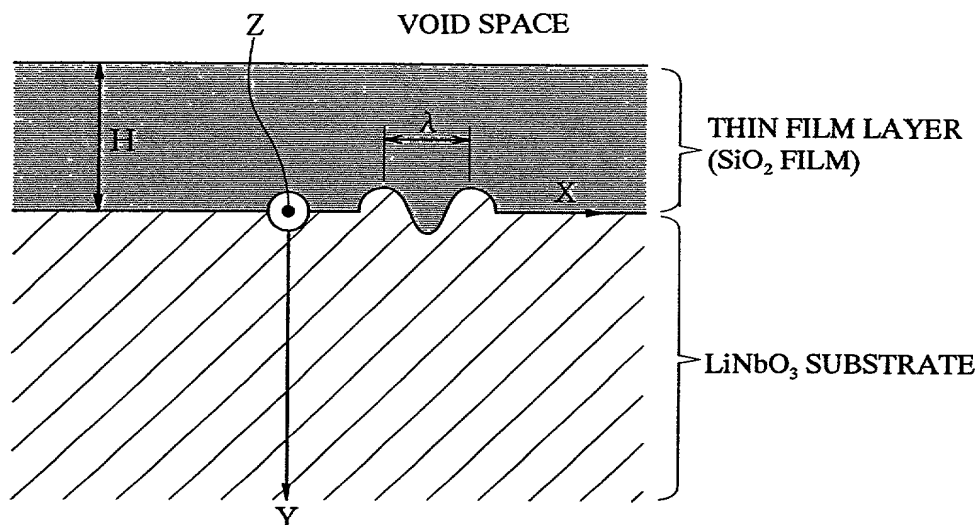


Fig.2
(10°)

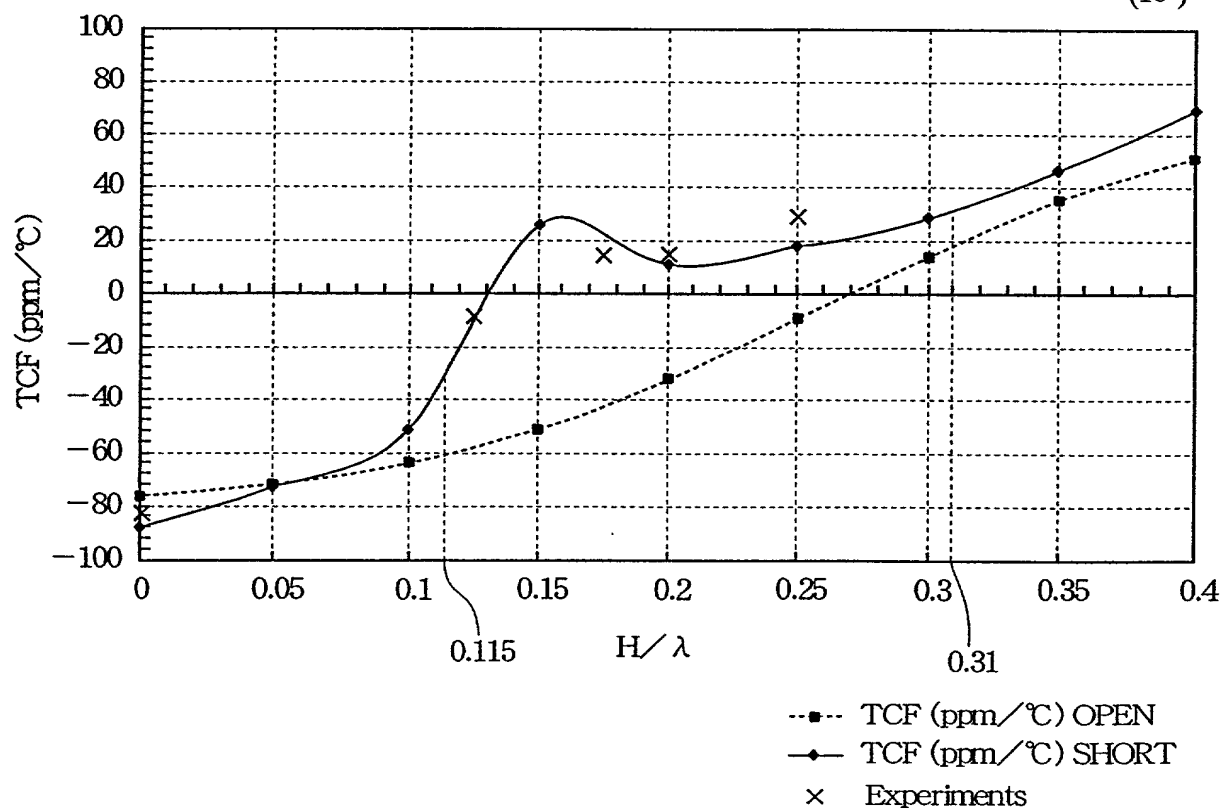
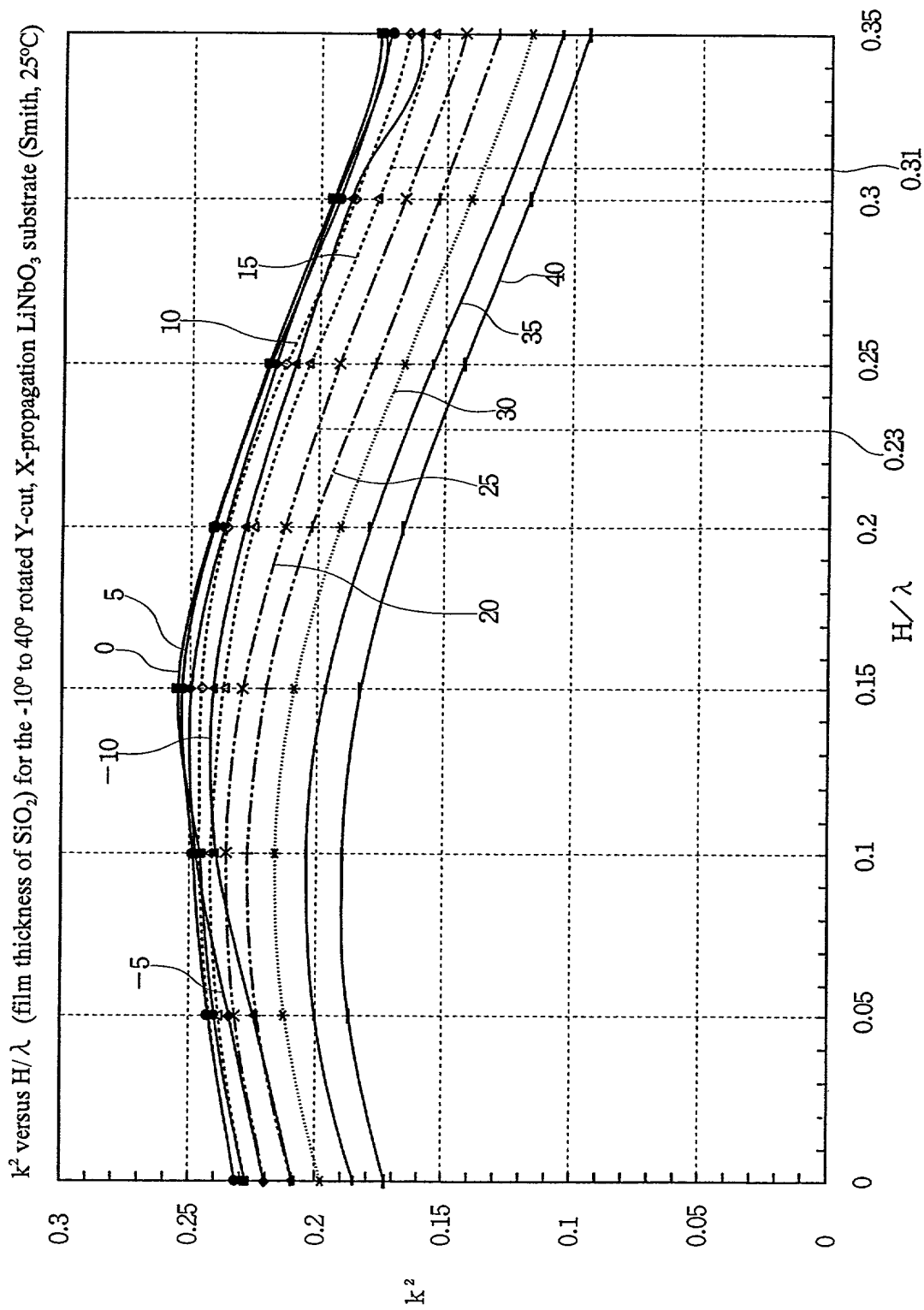


Fig.3



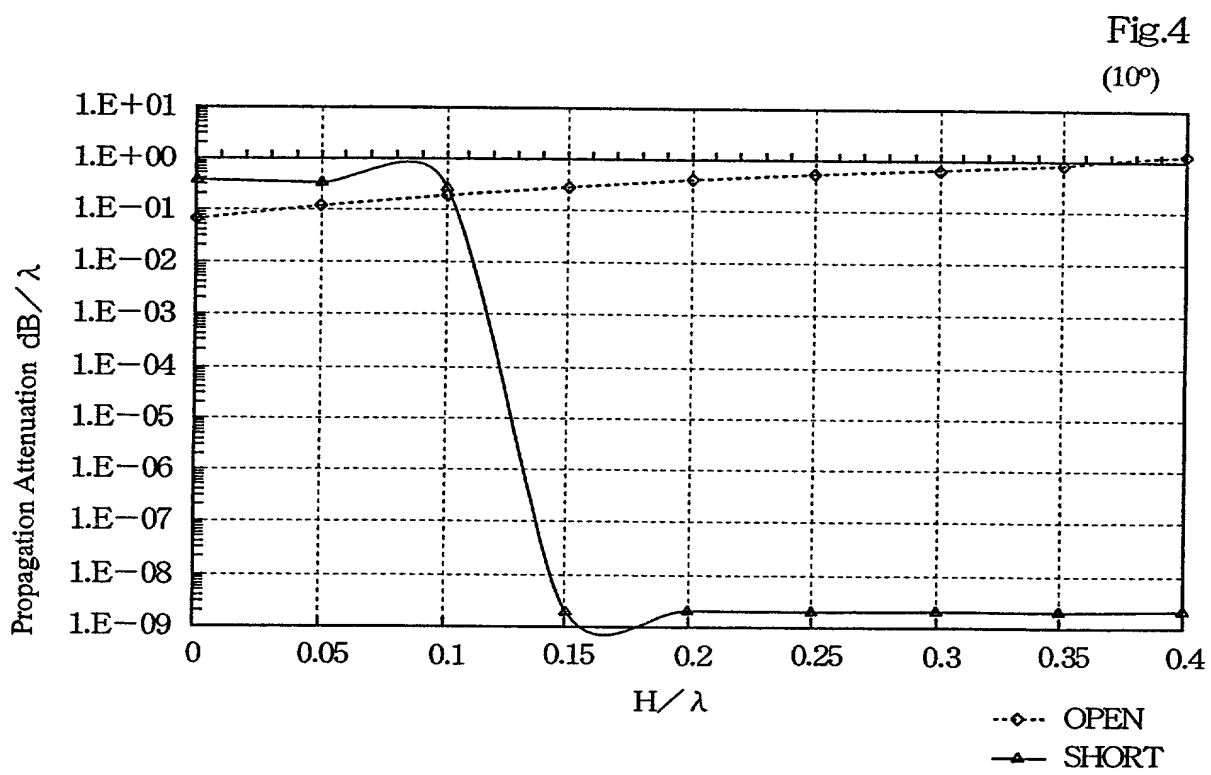


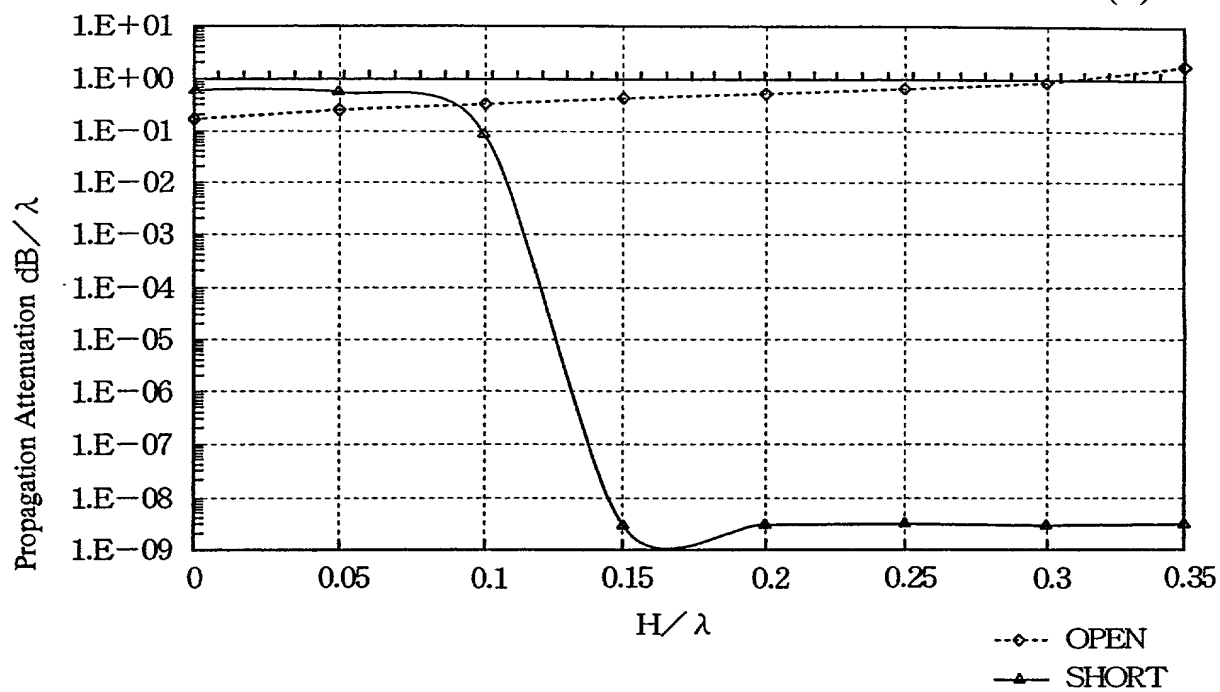
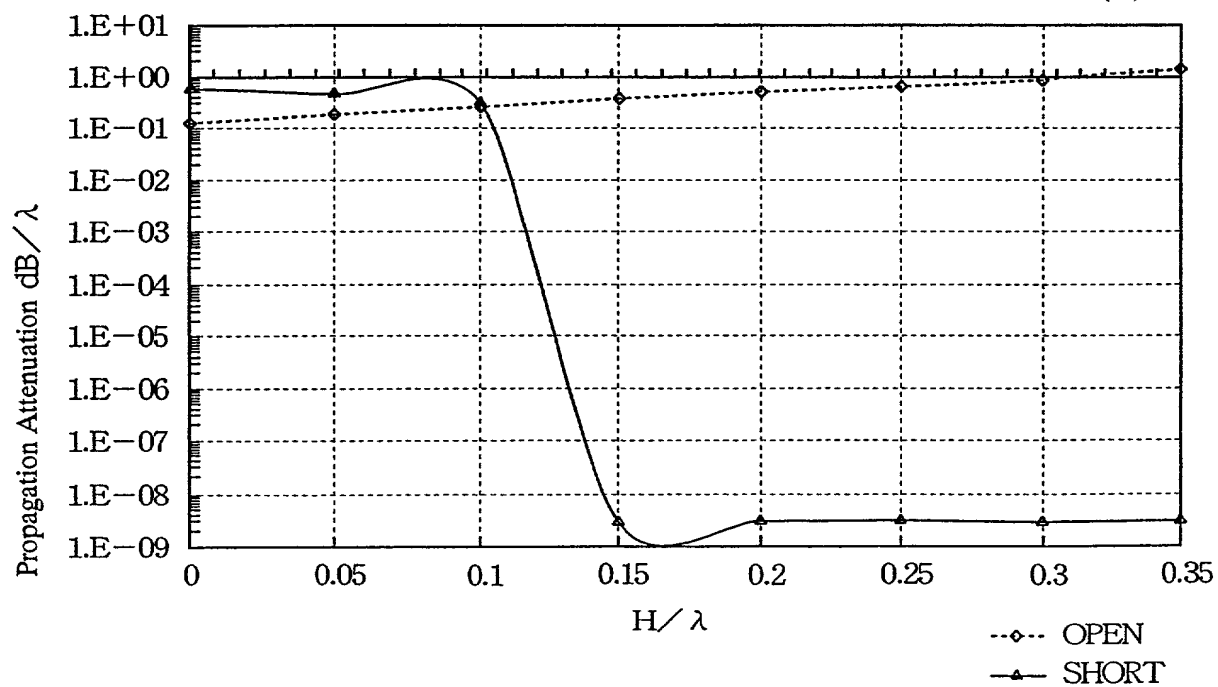
Fig.5
(0°)Fig.6
(5°)

Fig.7
(10°)

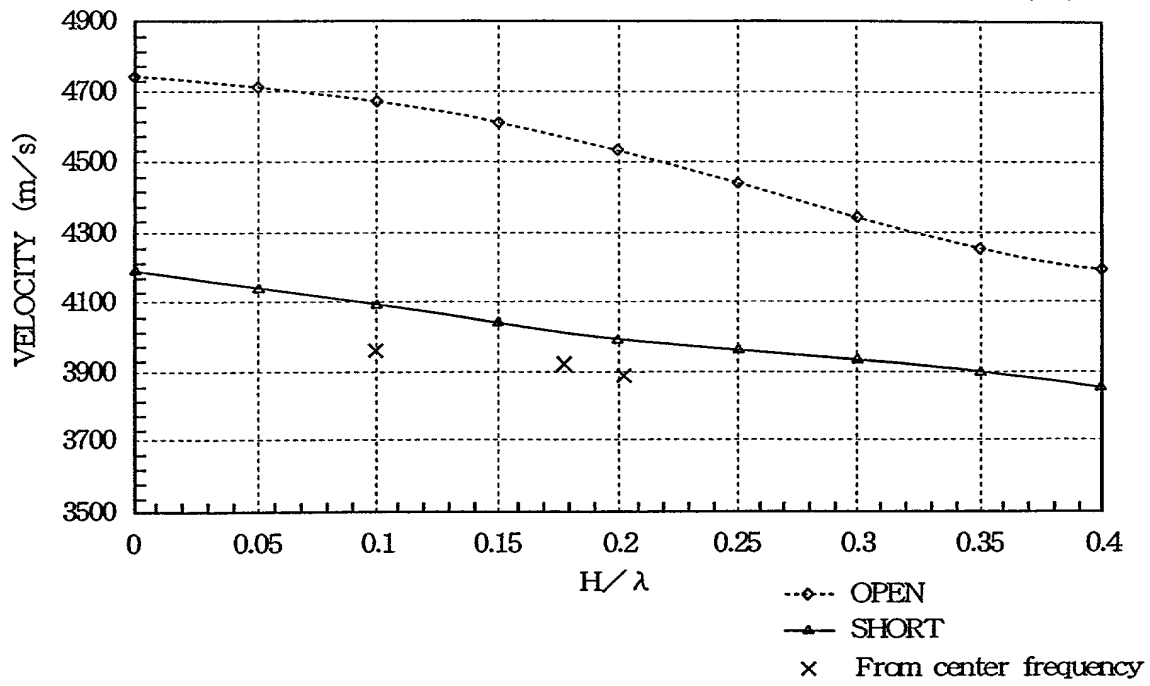


Fig.8

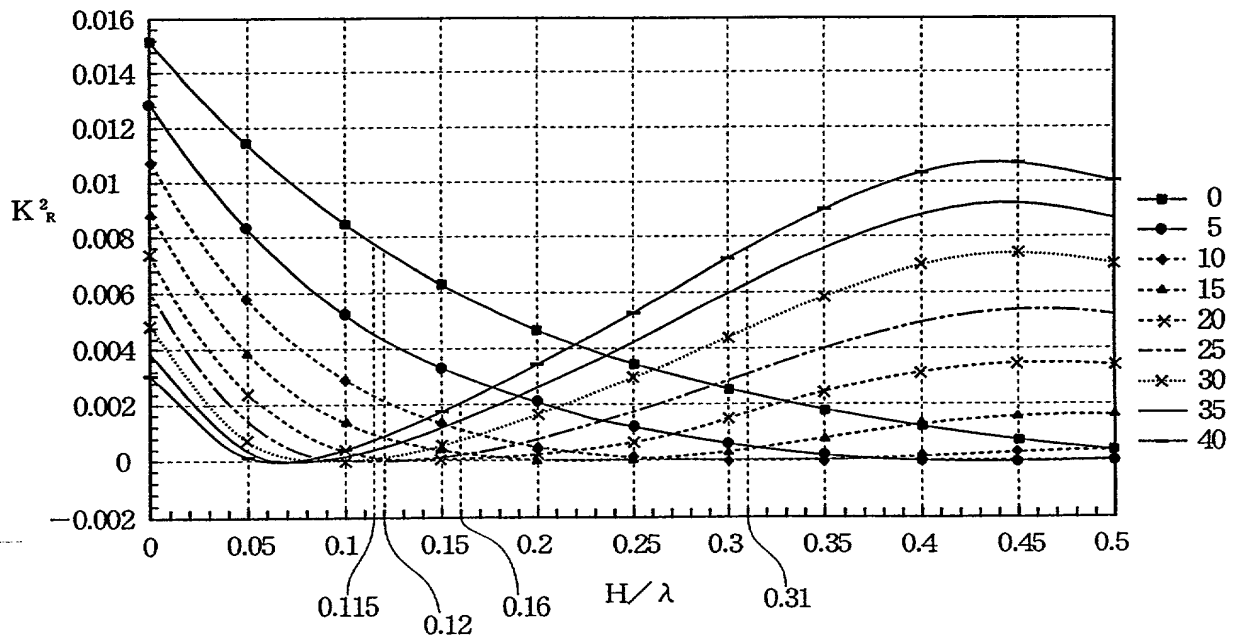


Fig. 9

TCF (ppm/°C) versus H/λ (film thickness of SiO_2) for SHORT of the 0° to 40° rotated Y-cut, X-propagation LiNbO_3 substrate (Smith constant)

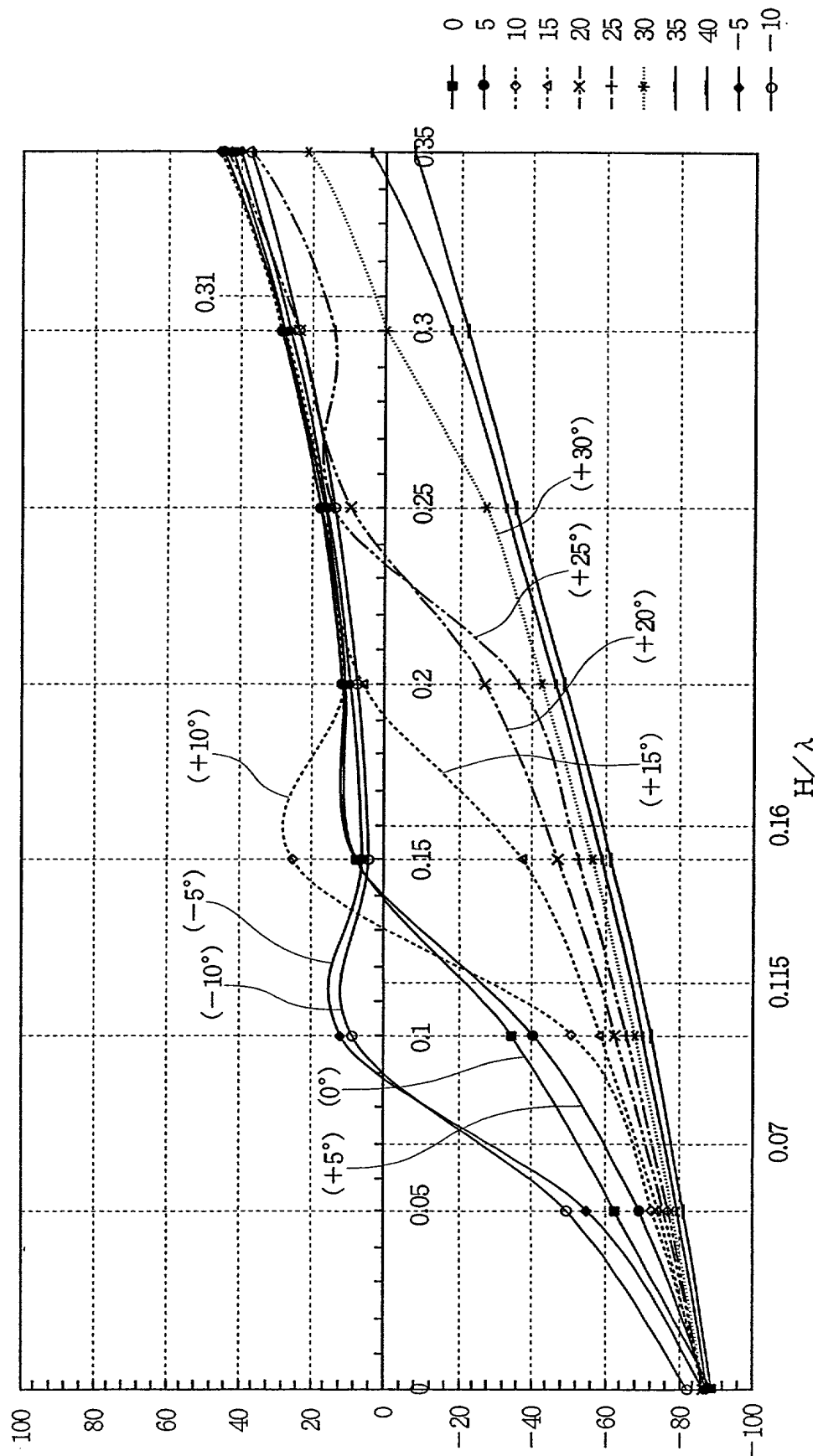


Fig.10

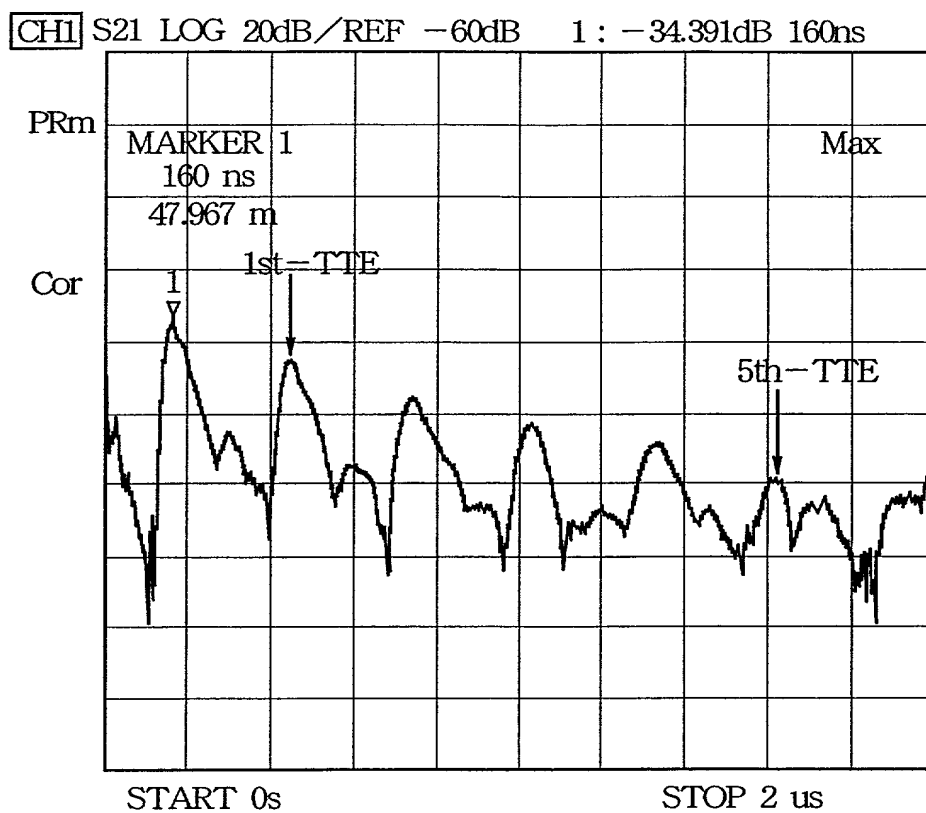


Fig.11

